

HM628127H/HM629127H Series

131072-word × 8/9-bit High Speed CMOS Static RAM

The HM628127H/HM629127H is an asynchronous high speed static RAM organized as 131,072-word × 8/9-bit. It realizes high speed access time (20/25 ns) with employing 0.8 μm CMOS process and high speed circuit designing technology.

It is most appropriate for the application which requires high speed, high density memory and wide bit width configuration, such as cache and buffer memory in system.

The HM628127H/HM629127H is packaged in 400-mil 32/36-pin SOJ for high density surface mounting.

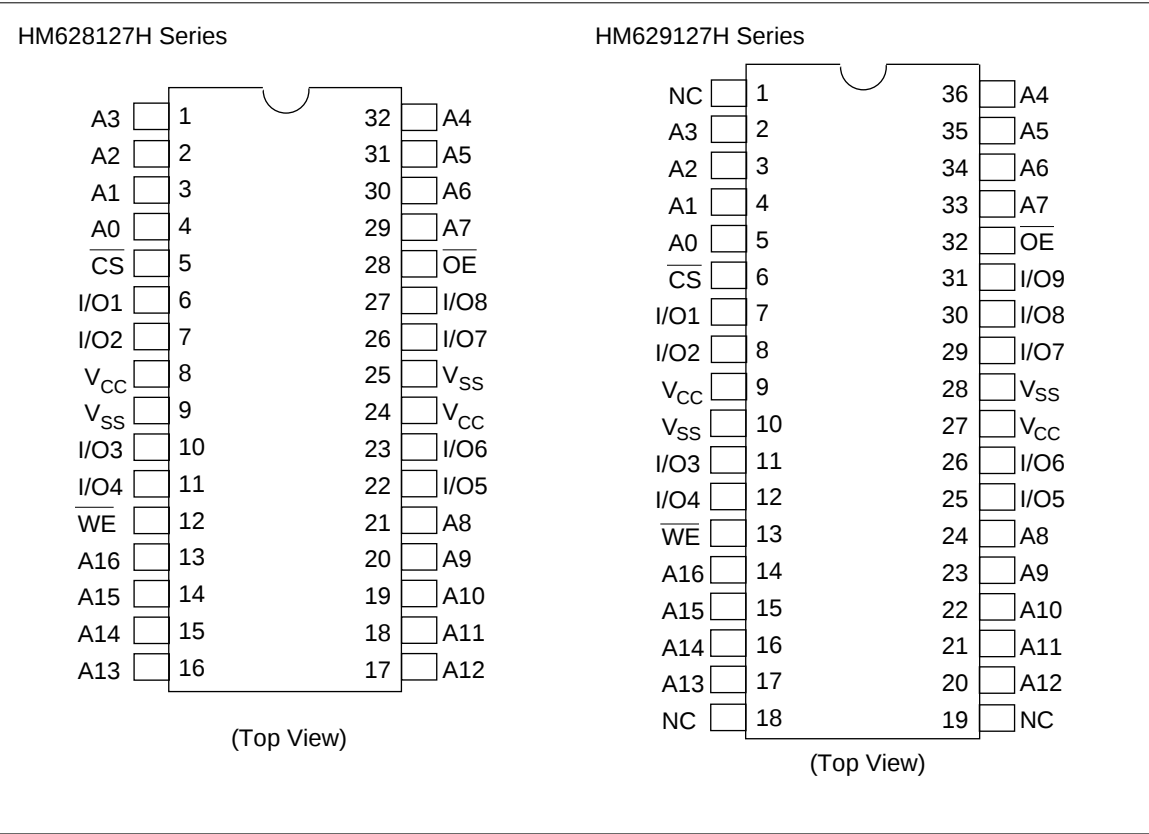
Features

- Single 5 V supply: 5 V ± 10%
- Access time 20/25 ns (max)
- Completely static memory
 - No clock or timing strobe required
- Equal access and cycle times
- Directly TTL compatible
 - All inputs and outputs
- 400-mil 32/36-pin SOJ package
- Center V_{CC} and V_{SS} type pinout

Ordering Information

Type No.	Access time	Package
HM628127HJP-20	20 ns	400-mil 32-pin plastic SOJ (CP-32DB)
HM628127HJP-25	25 ns	
HM628127HLJP-20	20 ns	
HM628127HLJP-25	25 ns	
HM629127HJP-20	20 ns	400-mil 36-pin Plastic SOJ (CP-36D)
HM629127HJP-25	25 ns	
HM629127HLJP-20	20 ns	
HM629127HLJP-25	25 ns	

Pin Arrangement

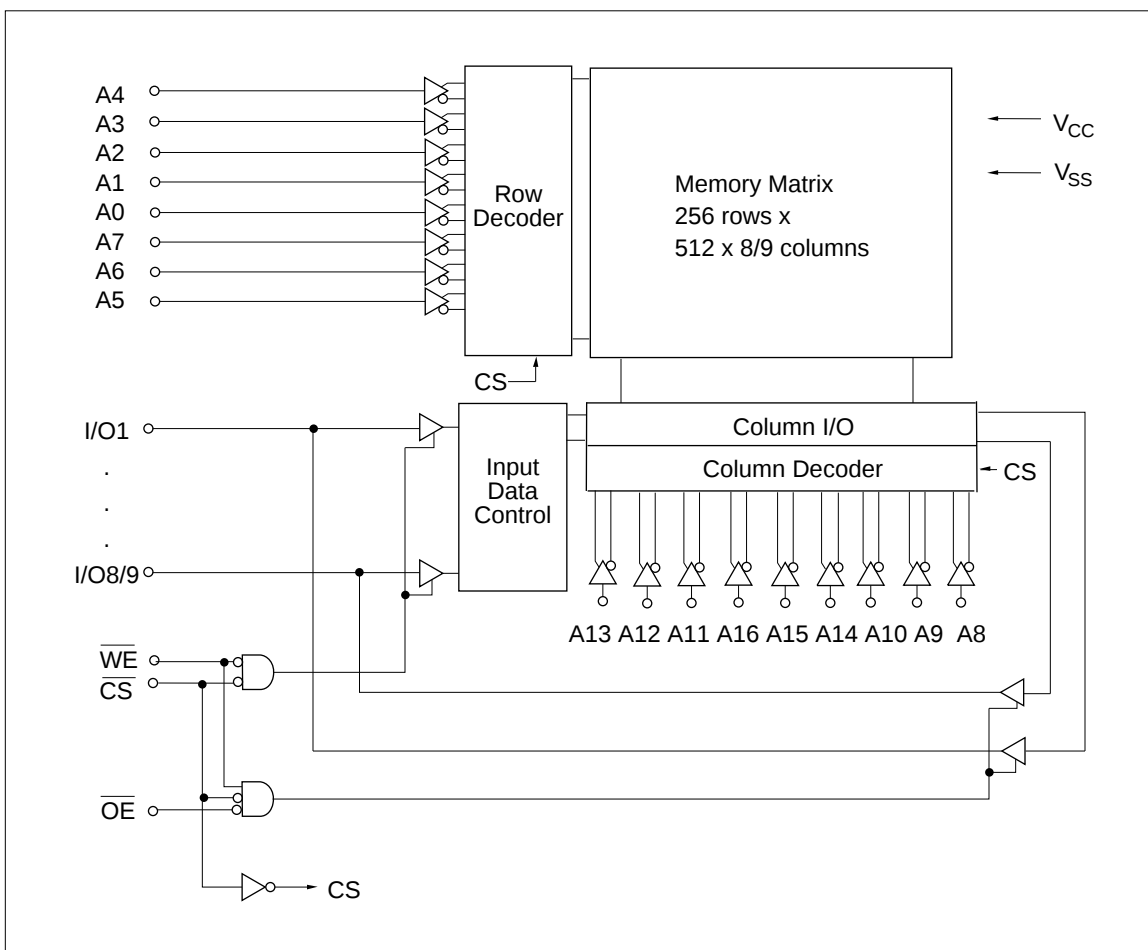


Pin Description

Pin name

HM628127H	HM629127H	Function
A0 – A16	A0 – A16	Address
I/O1 – I/O8	I/O1 – I/O9	Data input/output
$\overline{\text{CS}}$	$\overline{\text{CS}}$	Chip select
$\overline{\text{WE}}$	$\overline{\text{WE}}$	Write enable
$\overline{\text{OE}}$	$\overline{\text{OE}}$	Output enable
V_{CC}	V_{CC}	Power supply
V_{SS}	V_{SS}	Ground
—	NC	No connection

Block Diagram



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply voltage relative to V_{SS}	V_{CC}	-0.5 to +7.0	V
Voltage on any pin relative to V_{SS}	V_T	-0.5 ^{*1} to $V_{CC} + 0.5$	V
Power dissipation	P_T	1.0 ^{*2} / 1.5 ^{*3}	W
Operating temperature	T_{opr}	0 to +70	°C
Storage temperature	T_{stg}	-55 to +125	°C
Storage temperature under bias	T_{bias}	-10 to +85	°C

Note: 1. -2.5 V for pulse width (under shoot) ≤ 10 ns
 2. at still air condition
 3. at air flow ≥ 1.0 m/s

Function Table

$\overline{\text{CS}}$	$\overline{\text{OE}}$	$\overline{\text{WE}}$	V_{CC} current	I/O	Ref. cycle
H	X	X	$I_{\text{SB}}, I_{\text{SB1}}$	High-Z	—
L	H	H	I_{CC}	High-Z	—
L	L	H	I_{CC}	Output	Read cycle
L	X	L	I_{CC}	Input	Write cycle

Note: X: H or L

Recommended DC Operating Conditions ($T_a = 0$ to $+70^\circ\text{C}$)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage*2	V_{CC}	4.5	5.0	5.5	V
	V_{SS}	0	0	0	V
Input voltage	V_{IH}	2.2	—	$V_{\text{CC}} + 0.5$	V
	V_{IL}	-0.5^{*1}	—	0.8	V

Note: 1. -2.0 V for pulse width (under shoot) ≤ 10 ns
 2. The supply voltage with all V_{CC} pins must be on the same level.
 The supply voltage with all V_{SS} pins must be on the same level.

DC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 5\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Min	Typ* ¹	Max	Unit	Test conditions	Notes
Input leakage current	$ I_{LI} $	—	—	2	μA	$V_{in} = V_{SS}$ to V_{CC}	
Output leakage current	$ I_{LO} $	—	—	2	μA	$V_{I/O} = V_{SS}$ to V_{CC}	
Operating power supply current	I_{CC}	—	130	180	mA	20 ns cycle	$\overline{CS} = V_{IL}$, $I_{out} = 0\text{ mA}$ Other inputs $= V_{IH}/V_{IL}$
		—	100	160	mA	25 ns cycle	
Standby power supply current	I_{SB}	—	50	90	mA	20 ns cycle	$\overline{CS} = V_{IH}$, Other inputs $= V_{IH}/V_{IL}$
		—	40	85	mA	25 ns cycle	
Standby power supply current (1)	I_{SB1}	—	—	2	mA	$V_{CC} \geq \overline{CS} \geq V_{CC} - 0.2\text{ V}$, $0\text{ V} \leq V_{in} \leq 0.2\text{ V}$ or	L-version
		—	—	0.2	mA	$V_{CC} \geq V_{in} \geq V_{CC} - 0.2\text{ V}$	
Output voltage	V_{OL}	—	—	0.4	V	$I_{OL} = 8\text{ mA}$	
	V_{OH}	2.4	—	—	V	$I_{OH} = -4\text{ mA}$	

Note: 1. Typical values are at $V_{CC} = 5.0\text{ V}$, $T_a = +25^\circ\text{C}$ and specified loading.

Capacitance ($T_a = 25^\circ\text{C}$, $f = 1.0\text{ MHz}$)*¹

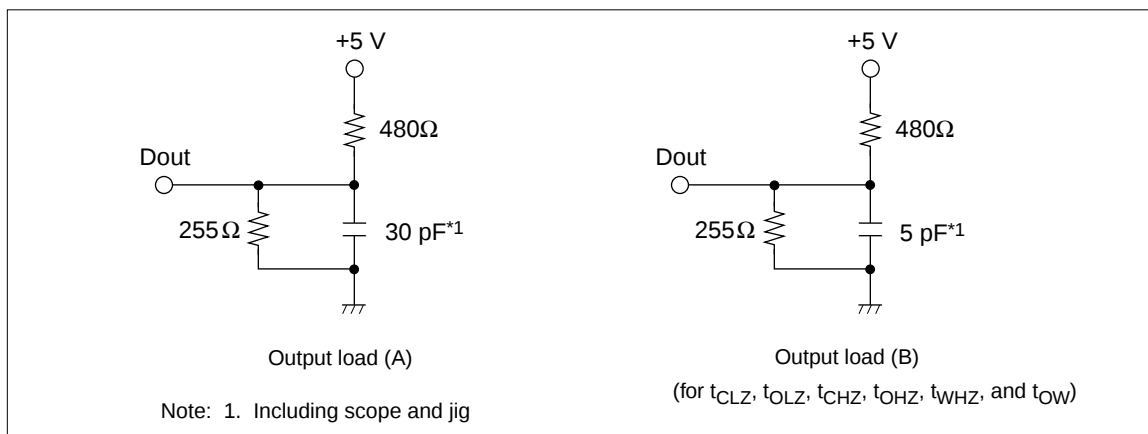
Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Input capacitance	C_{in}	—	—	6	pF	$V_{in} = 0\text{ V}$
Input/output capacitance	$C_{I/O}$	—	—	8	pF	$V_{I/O} = 0\text{ V}$

Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 5\text{ V} \pm 10\%$, unless otherwise noted.)

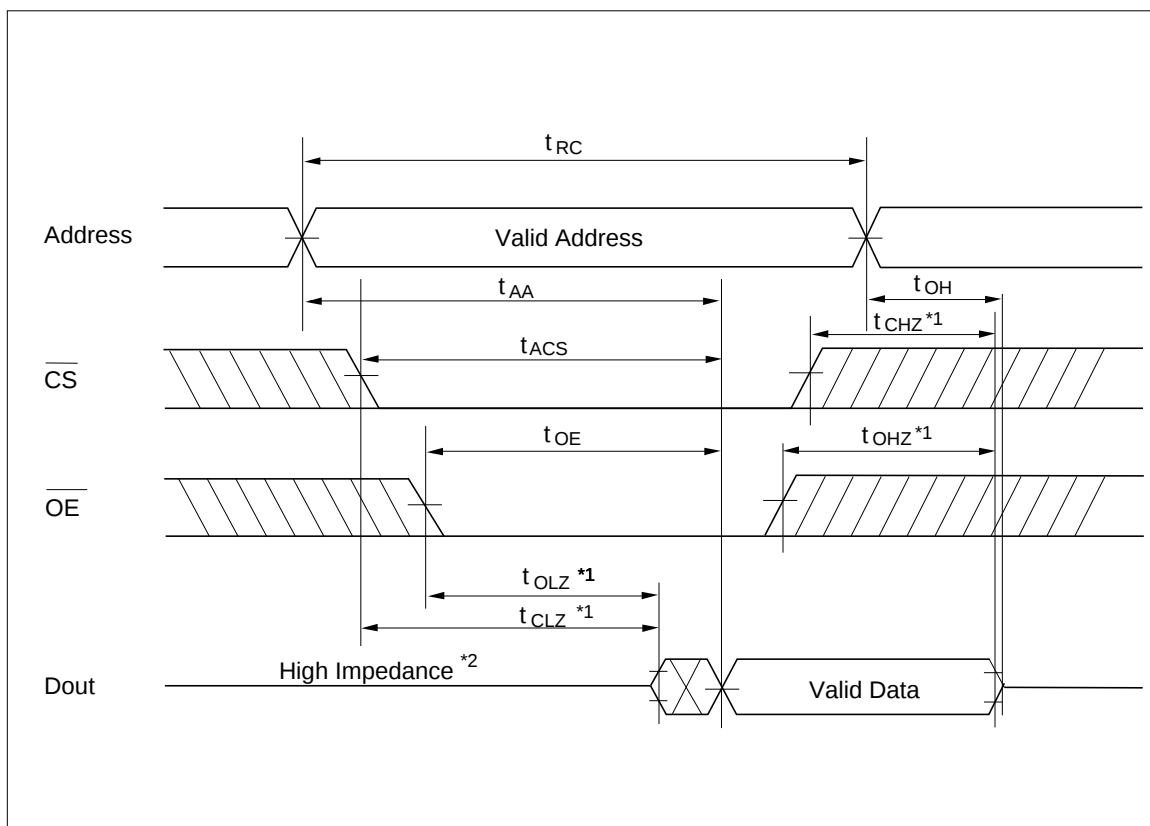
Test Conditions

- Input pulse levels: V_{SS} to 3.0 V
- Input rise and fall times: 3 ns
- Input and output timing reference levels: 1.5 V
- Output load: See figures



Read Cycle

Parameter	Symbol	HM628127H/HM629127H					
		-20		-25		Unit	
		Min	Max	Min	Max		
Read cycle time	t_{RC}	20	—	25	—	ns	
Address access time	t_{AA}	—	20	—	25	ns	
Chip select access time	t_{ACS}	—	20	—	25	ns	
Output enable to output valid	t_{OE}	—	10	—	12	ns	
Output hold from address change	t_{OH}	5	—	5	—	ns	
Chip select to output in low-Z	t_{CLZ}	3	—	3	—	ns	
Output enable to output in low-Z	t_{OLZ}	1	—	1	—	ns	
Chip deselect to output in high-Z	t_{CHZ}	—	7	—	7	ns	
Output disable to output in high-Z	t_{OHZ}	—	7	—	7	ns	

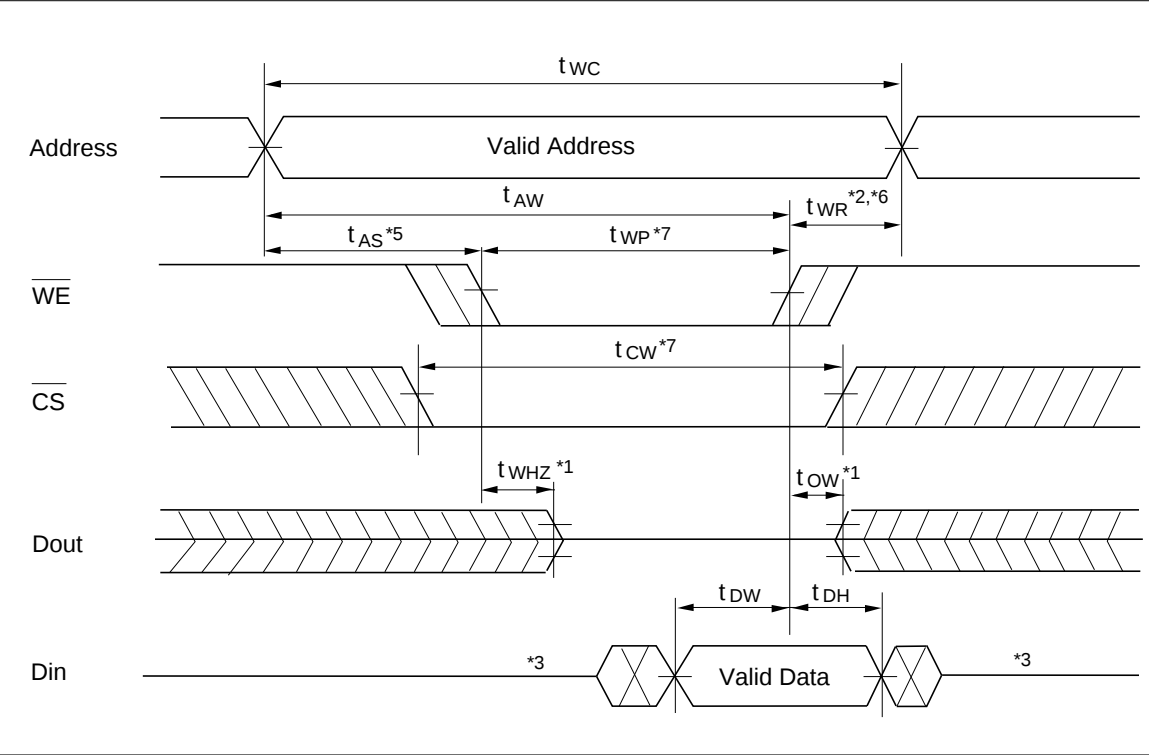
Read Timing Waveform^{*3}

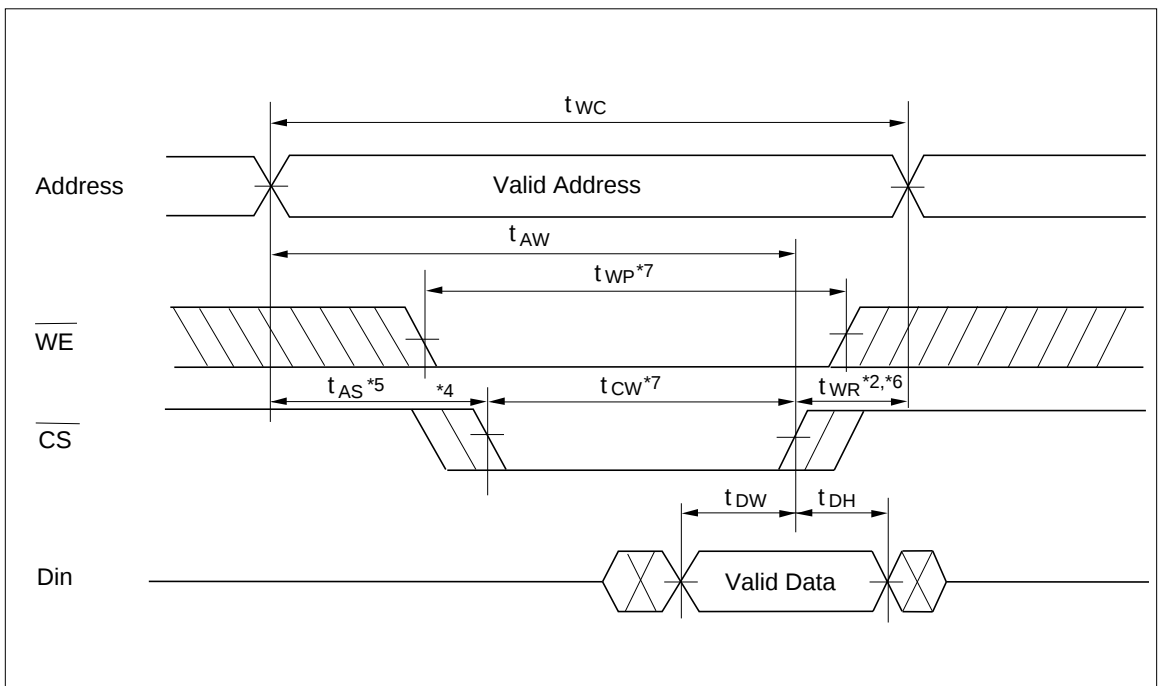
- Notes:
1. Transition is measured ± 200 mV from steady state's voltage with Load (B). This parameter is sampled and not 100% tested.
 2. When $\overline{CS}$ and $\overline{OE}$ are low, Dout is low impedance.
 3. $\overline{WE}$ is high for read cycle.

Write Cycle

		HM628127H/HM629127H				
		-20		-25		
Parameter	Symbol	Min	Max	Min	Max	Unit
Write cycle time	t _{WC}	20	—	25	—	ns
Address valid to end of write	t _{AW}	15	—	20	—	ns
Chip select to end of write	t _{CW}	12	—	12	—	ns
Write pulse width	t _{WP}	12	—	12	—	ns
Address setup time	t _{AS}	0	—	0	—	ns
Write recovery time	t _{WR}	0	—	0	—	ns
Data to write time overlap	t _{DW}	10	—	10	—	ns
Data hold from write time	t _{DH}	0	—	0	—	ns
Write disable to output in low-Z	t _{OW}	3	—	3	—	ns
Write enable to output in high-Z	t _{WHZ}	—	7	—	7	ns

Write Timing Waveform (1) ($\overline{WE}$ Controlled)



Write Timing Waveform (2) ($\overline{\text{CS}}$ Controlled)

- Notes:
1. Transition is measured ± 200 mV from high impedance state's voltage with Load (B). This parameter is sampled and not 100% tested.
 2. $\overline{\text{WE}}$ must be high during transition except when the device is disabled with $\overline{\text{CS}}$.
 3. If $\overline{\text{CS}}$ and $\overline{\text{OE}}$ are low during this period, I/O pins are in the output state. Then, the data input signals of opposite phase to the outputs must not be applied to them.
 4. If the $\overline{\text{CS}}$ low transition occurs simultaneously with the $\overline{\text{WE}}$ low transition or after the $\overline{\text{WE}}$ transition, output remains a high impedance state.
 5. t_{AS} is from the latest address change to the latest transition (High to Low) of $\overline{\text{WE}}$ or $\overline{\text{CS}}$.
 6. t_{WR} is from the first transition (Low to High) of $\overline{\text{WE}}$ or $\overline{\text{CS}}$ to the first address transition.
 7. A write occurs during the overlap of a low $\overline{\text{WE}}$ and a low $\overline{\text{CS}}$.

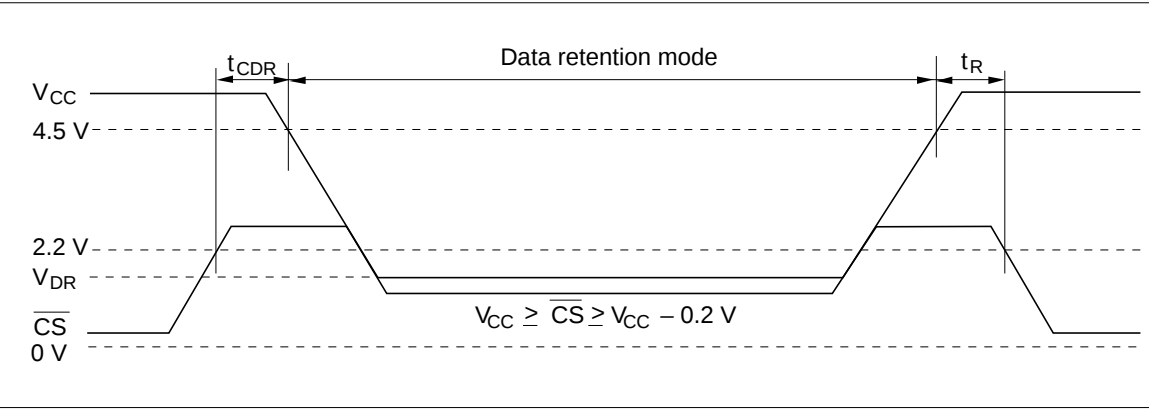
Low V_{CC} Data Retention Characteristics (T_a = 0 to +70°C)

This characteristics is guaranteed only for L-version.

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
V _{CC} for data retention	V _{DR}	2.0	—	—	V	V _{CC} ≥ $\overline{CS}$ ≥ V _{CC} - 0.2 V,
Data retention current	I _{CCDR}	—	2	80*1	μA	V _{CC} ≥ V _{in} ≥ V _{CC} - 0.2 V or
Chip deselect to data retention time	t _{CDR}	0	—	—	ns	0 V ≤ V _{in} ≤ 0.2 V
Operation recovery time	t _R	5	—	—	ms	

Note: 1. V_{CC} = 3.0 V

Low V_{CC} Data Retention Timing Waveform



HM628127HB Series

Preliminary

131072-word × 8-bit High Speed CMOS Static RAM

HITACHI

Rev. 0.0

The HM628127HB is an asynchronous high speed static RAM organized as 128-kword × 8-bit. It realize high speed access time (15/20/25 ns) with employing 0.8 μ m shrink CMOS process and high speed circuit designing technology.

It is most appropriate for the application which requires high speed, high density memory and wide bit width configuration, such as cache and buffer memory in system.

The HM628127HB is packaged in 400-mil 32-pin SOJ for high density surface mounting.

Features

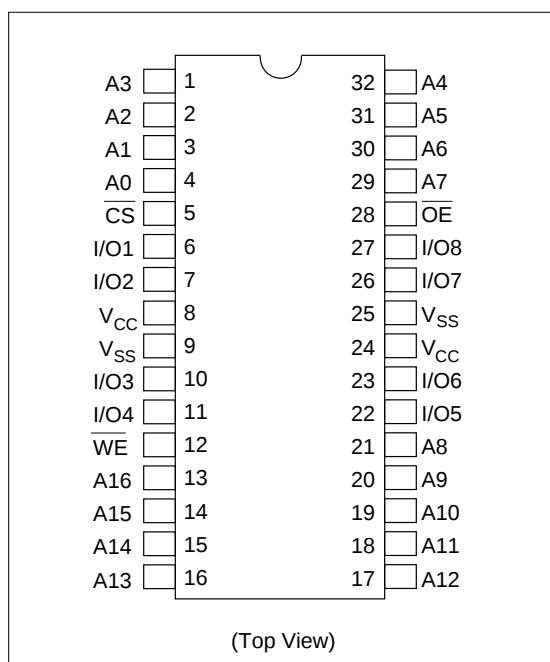
- Single 5 V supply: 5 V $\pm$ 10%
- Access time 15/20/25 ns (max)
- Completely static memory
 - No clock or timing strobe required
- Equal access and cycle times
- Directly TTL compatible
 - All inputs and outputs
- 400-mil 32-pin SOJ package
- Center V_{CC} and V_{SS} type pinout

Ordering Information

Type No.	Access time	Package
HM628127HBJP-15	15 ns	400-mil 32-pin plastic SOJ (CP-32DB)
HM628127HBJP-20	20 ns	
HM628127HBJP-25	25 ns	
HM628127HBLJP-15	15 ns	
HM628127HBLJP-20	20 ns	
HM628127HBLJP-25	25 ns	

Preliminary: This document contains information on a new product. Specifications and information contained herein are subject to change without notice.

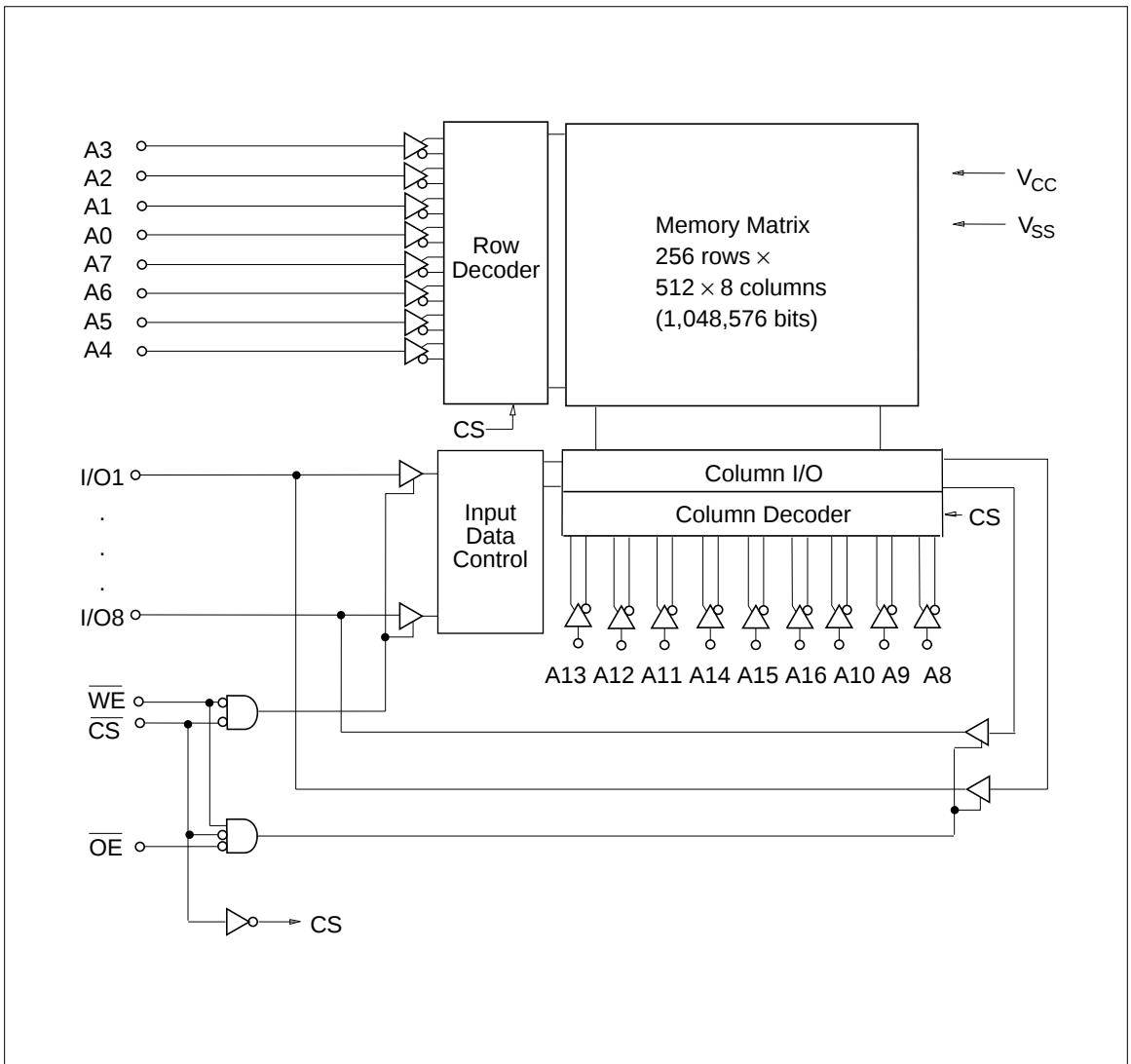
Pin Arrangement



Pin Description

Pin name	Function
A0 to A16	Address
I/O1 to I/O8	Input/output
$\overline{CS}$	Chip select
$\overline{OE}$	Output enable
$\overline{WE}$	Write enable
V_{CC}	Power supply
V_{SS}	Ground

Block Diagram



Absolute Maximum Ratings

Parameter	Symbol	Value	Unit
Supply voltage relative to V_{SS}	V_{CC}	-0.5 to +7.0	V
Voltage on any pin relative to V_{SS}	V_T	-0.5 *1 to $V_{CC}+0.5$	V
Power dissipation	P_T	1.0*2 / 1.5*3	W
Operating temperature	T_{opr}	0 to +70	°C
Storage temperature	T_{stg}	-55 to +125	°C
Storage temperature under bias	T_{bias}	-10 to +85	°C

Note: 1. -2.5 V for pulse width (under shoot) ≤ 10 ns
 2. at still air condition
 3. at air flow ≥ 1.0 m/s

Function Table

$\overline{CS}$	$\overline{OE}$	$\overline{WE}$	V_{CC} current	I/O	Ref. cycle
H	X	X	I_{SB}, I_{SB1}	High-Z	—
L	H	H	I_{CC}	High-Z	—
L	L	H	I_{CC}	Output	Read cycle
L	X	L	I_{CC}	Input	Write cycle

Note: 1. X: H or L

Recommended DC Operating Conditions ($T_a = 0$ to +70°C)

Parameter	Symbol	Min	Typ	Max	Unit
Supply voltage*2	V_{CC}	4.5	5.0	5.5	V
	V_{SS}	0	0	0	V
Input voltage	V_{IH}	2.2	—	$V_{CC}+0.5$	V
	V_{IL}	-0.5 *1	—	0.8	V

Note: 1. -2.0 V for pulse width (under shoot) ≤ 10 ns
 2. The supply voltage with all V_{CC} pins must be on the same level.
 The supply voltage with all V_{SS} pins must be on the same level.

DC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 5\text{ V} \pm 10\%$, $V_{SS} = 0\text{ V}$)

Parameter	Symbol	Min	Typ*1	Max	Unit	Test conditions	Notes
Input leakage current	$ I_{LI} $	—	—	2	μA	$V_{in} = V_{SS}$ to V_{CC}	
Output leakage current	$ I_{LO} $	—	—	2	μA	$V_{I/O} = V_{SS}$ to V_{CC}	1
Operating power supply current	I_{CC}	—	120	180	mA	15 ns cycle $\overline{CS} = V_{IL}$, $I_{out} = 0\text{ mA}$	Other inputs $= V_{IH}/V_{IL}$
		—	100	150	mA	20 ns cycle	
		—	85	130	mA	25 ns cycle	
Standby power supply current	I_{SB}	—	55	100	mA	15 ns cycle $\overline{CS} = V_{IH}$, Other inputs $= V_{IH}/V_{IL}$	
		—	45	80	mA	20 ns cycle	
		—	40	70	mA	25 ns cycle	
Standby power supply current (1)	I_{SB1}	—	—	2	mA	$V_{CC} \geq \overline{CS} \geq V_{CC} - 0.2\text{ V}$, $0\text{ V} \leq V_{in} \leq 0.2\text{ V}$ or	L-version
		—	—	0.2	mA	$V_{CC} \geq V_{in} \geq V_{CC} - 0.2\text{ V}$	
Output voltage	V_{OL}	—	—	0.4	V	$I_{OL} = 8\text{ mA}$	
	V_{OH}	2.4	—	—	V	$I_{OH} = -4\text{ mA}$	

Note: 1. Typical values are at $V_{CC} = 5.0\text{ V}$, $T_a = +25^\circ\text{C}$ and specified loading.

Capacitance ($T_a = 25^\circ\text{C}$, $f = 1.0\text{ MHz}$)*1

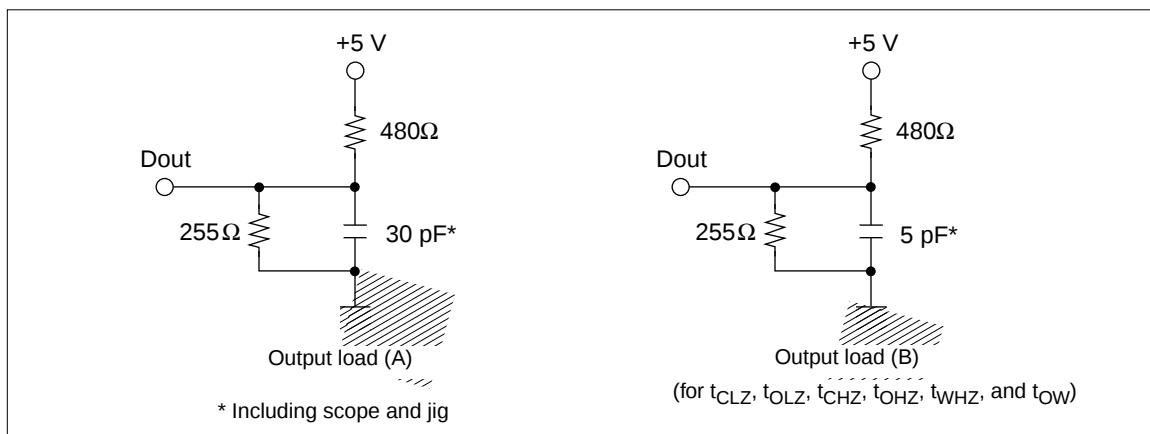
Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
Input capacitance	C_{in}	—	—	6	pF	$V_{in} = 0\text{ V}$
Input/output capacitance	$C_{I/O}$	—	—	8	pF	$V_{I/O} = 0\text{ V}$

Note: 1. This parameter is sampled and not 100% tested.

AC Characteristics ($T_a = 0$ to $+70^\circ\text{C}$, $V_{CC} = 5\text{ V} \pm 10\%$, unless otherwise noted.)

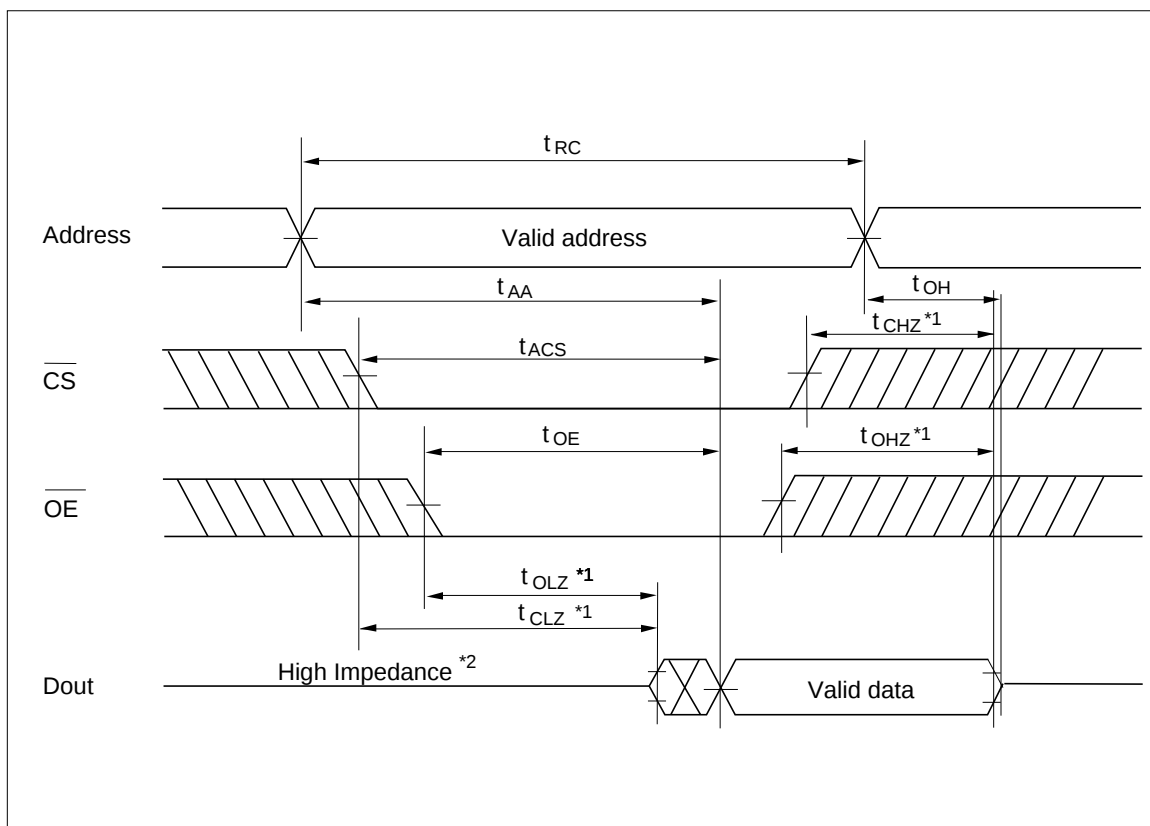
Test Conditions

- Input pulse levels: V_{SS} to 3.0 V
- Input rise and fall times: 3 ns
- Input and output timing reference levels: 1.5 V
- Output load: See figures



Read Cycle

		HM628127HB						
		-15		-20		-25		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit
Read cycle time	t _{RC}	15	—	20	—	25	—	ns
Address access time	t _{AA}	—	15	—	20	—	25	ns
Chip select access time	t _{ACS}	—	15	—	20	—	25	ns
Output enable to output valid	t _{OE}	—	8	—	10	—	12	ns
Output hold from address change	t _{OH}	5	—	5	—	5	—	ns
Chip select to output in low-Z	t _{CLZ}	3	—	3	—	3	—	ns
Output enable to output in low-Z	t _{OLZ}	1	—	1	—	1	—	ns
Chip deselect to output in high-Z	t _{CHZ}	—	7	—	7	—	7	ns
Output disable to output in high-Z	t _{OHZ}	—	7	—	7	—	7	ns

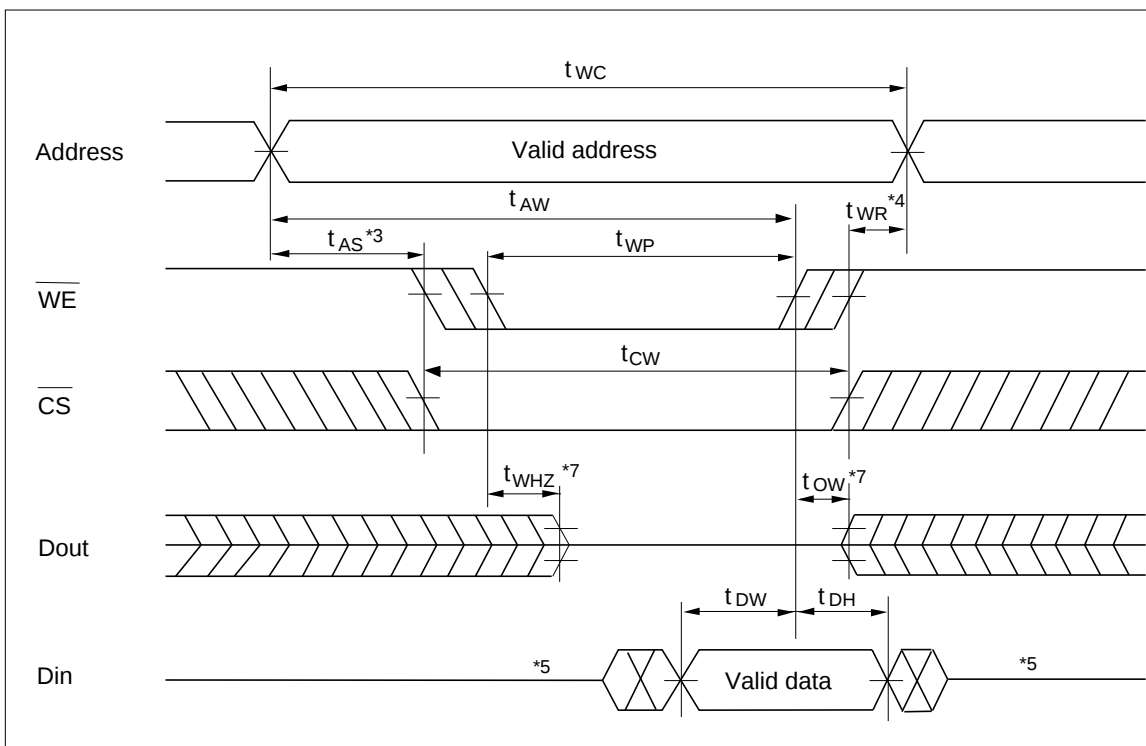
Read Timing Waveform^{*3}

- Notes:
1. Transition is measured ± 200 mV from steady voltage with Load (B). This parameter is sampled and not 100% tested.
 2. When $\overline{CS}$ and $\overline{OE}$ are low, Dout is low impedance.
 3. $\overline{WE}$ is high for read cycle.

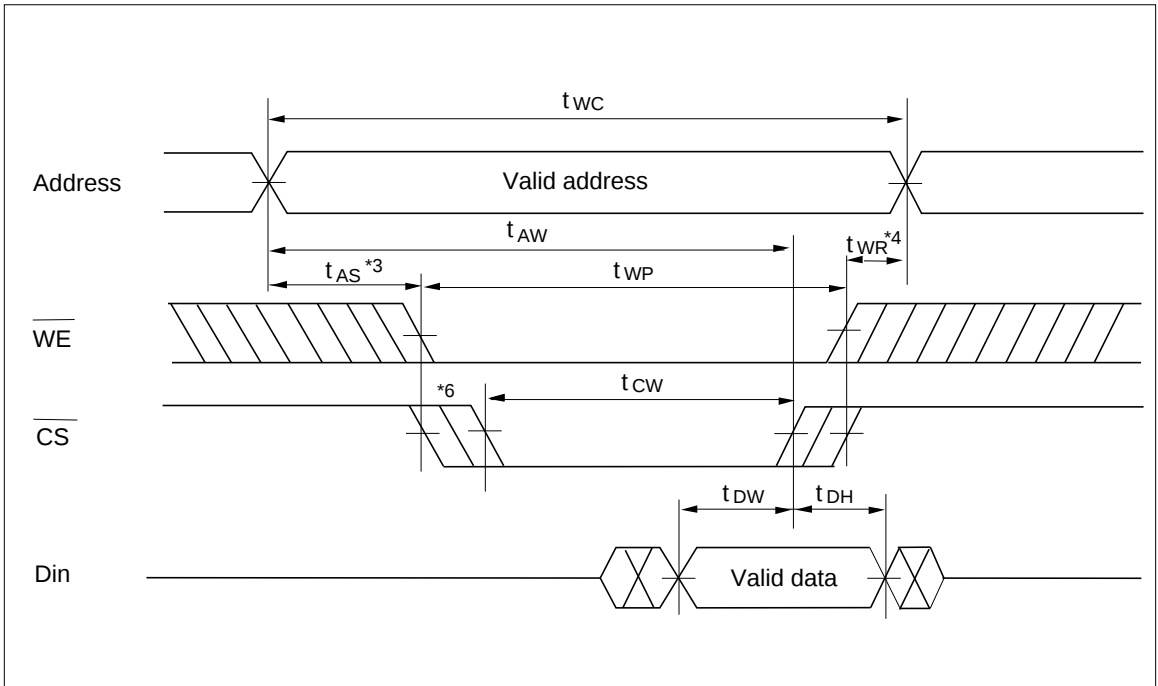
Write Cycle

		HM628127HB						
		-15		-20		-25		
Parameter	Symbol	Min	Max	Min	Max	Min	Max	Unit
Write cycle time	t _{WC}	15	—	20	—	25	—	ns
Address valid to end of write	t _{AW}	12	—	15	—	15	—	ns
Chip select to end of write	t _{CW}	10	—	12	—	12	—	ns
Write pulse width	t _{WP}	10	—	12	—	12	—	ns
Address setup time	t _{AS}	0	—	0	—	0	—	ns
Write recovery time	t _{WR}	0	—	0	—	0	—	ns
Data to write time overlap	t _{DW}	8	—	10	—	10	—	ns
Data hold from write time	t _{DH}	0	—	0	—	0	—	ns
Write disable to output in low-Z	t _{OW}	3	—	3	—	3	—	ns
Write enable to output in high-Z	t _{WHZ}	—	7	—	7	—	7	ns

Write Timing Waveform (1) ($\overline{WE}$ Controlled)



Write Timing Waveform (2) ($\overline{\text{CS}}$ Controlled)



Low V_{CC} Data Retention Characteristics ($T_a = 0$ to $+70^\circ\text{C}$)

This characteristics is guaranteed only for L-version.

Parameter	Symbol	Min	Typ	Max	Unit	Test conditions
V_{CC} for data retention	V_{DR}	2.0	—	—	V	$V_{CC} \geq \overline{CS} \geq V_{CC} - 0.2 \text{ V}$, $V_{CC} \geq V_{in} \geq V_{CC} - 0.2 \text{ V}$ or $0 \text{ V} \leq V_{in} \leq 0.2 \text{ V}$
Data retention current	I_{CCDR}	—	2	80^{*1}	μA	
Chip deselect to data retention time	t_{CDR}	0	—	—	ns	
Operation recovery time	t_R	5	—	—	ms	

Note: 1. $V_{CC} = 3.0 \text{ V}$

Low V_{CC} Data Retention Timing Waveform

